

# BD810

Silicon PNP Transistors



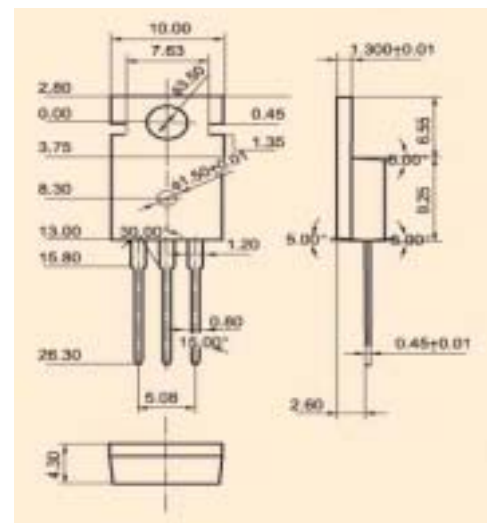
**B C E**

### ◆ Features

- . Designed for use in high power audio amplifiers utilizing complementary or quasi complementary circuits.
- . With TO-220 package

### ◆ Absolute Maximum Ratings Tc=25°C

SYMBOL	PARAMETER	RATING	UNIT
V <sub>CB0</sub>	Collector to base voltage	80	V
V <sub>CEO</sub>	Collector to emitter voltage	80	V
V <sub>EBO</sub>	Emitter to base voltage	5.0	V
I <sub>B</sub>	Base collector current	6.0	A
I <sub>C</sub>	Collector current	10	A
P <sub>C</sub>	Collector power dissipation	90	W
T <sub>j</sub>	Junction temperature	150	°C
T <sub>stg</sub>	Storage temperature	-55~150	°C



TO-220

### ◆ Electrical Characteristics Tc=25°C

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
I <sub>CB0</sub>	Collector-base cut-off current	V <sub>CB</sub> =80V; I <sub>E</sub> =0			1.0	mA
I <sub>EBO</sub>	Emitter-base cut-off current	V <sub>EB</sub> =5.0V; I <sub>C</sub> =0			2.0	mA
I <sub>CEO</sub>	Collector-emitter cut-off current					
V <sub>CB0</sub>	Collector-base breakdown voltage					
V <sub>(BR)ceo</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =0.1A; I <sub>B</sub> =0	80			V
V <sub>EBO</sub>	Emitter-base breakdown voltage					
V <sub>CE(sat-1)</sub>	Collector-emitter saturation voltages	I <sub>C</sub> =3A; I <sub>B</sub> =0.3A			1.1	V
V <sub>CE(sat-2)</sub>	Collector-emitter saturation voltages					
h <sub>FE-1</sub>	Forward current transfer ratio	I <sub>C</sub> =2A; V <sub>CE</sub> =2V	30			
h <sub>FE-2</sub>	Forward current transfer ratio	I <sub>C</sub> =4A; V <sub>CE</sub> =2V	15			
h <sub>FE-3</sub>	Forward current transfer ratio					
V <sub>BE(on)1</sub>	Base-emitter on voltages	I <sub>C</sub> =4A; V <sub>CE</sub> =2V			1.6	V
V <sub>BE(on)2</sub>	Base-emitter on voltages					
f <sub>T</sub>	Transition frequency	V <sub>CE</sub> =10V; I <sub>C</sub> =1A; f=1MHz	1.5			MHz
C <sub>ob</sub>	Output Capacitance					